Silicon P Channel Power MOS FET High Speed Power Switching

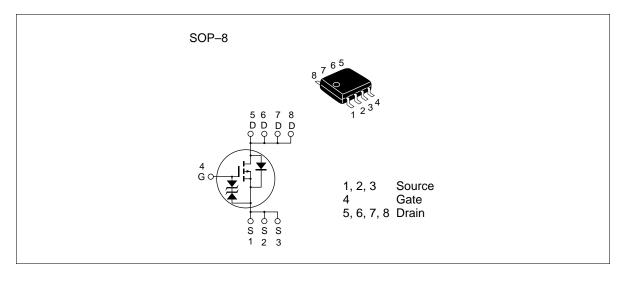
HITACHI

ADE-208-435 H (Z) 9th. Edition February 1999

Features

- Low on-resistance
- Capable of 4 V gate drive
- Low drive current
- High density mounting

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{\scriptscriptstyle DSS}$	- 30	V
Gate to source voltage	V _{GSS}	± 20	V
Drain current	I _D	- 5	A
Drain peak current	Note1	- 40	A
Body-drain diode reverse drain current	I _{DR}	- 5	A
Channel dissipation	Pch Note2	2.5	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. PW \leq 10 μ s, duty cycle \leq 1 %

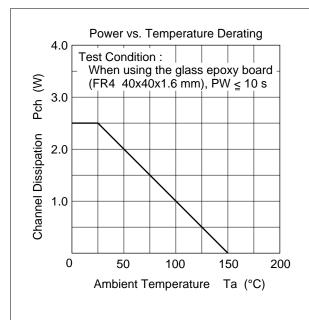
2. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW \leq 10s

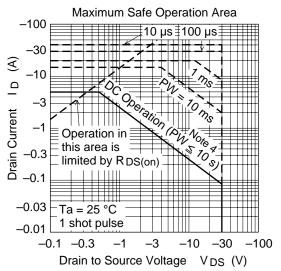
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	- 30	_	_	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	_	_	V	$I_{G} = \pm 100 \mu\text{A}, V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	± 10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltege drain current	I _{DSS}	_	_	-10	μΑ	$V_{DS} = -30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	- 1.0	_	- 2.5	V	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	0.04	0.07	Ω	$I_D = -3 \text{ A}, V_{GS} = -10 \text{ V}^{\text{Note3}}$
resistance	R _{DS(on)}	_	0.07	0.13	Ω	$I_D = -3 \text{ A}, V_{GS} = -4 \text{ V}^{\text{Note3}}$
Forward transfer admittance	y _{fs}	5.0	7.5	_	S	$I_D = -3 \text{ A}, V_{DS} = -10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss	_	860	_	pF	V _{DS} = - 10 V
Output capacitance	Coss	_	560	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	165	_	pF	f = 1MHz
Turn-on delay time	t _{d(on)}	_	30	_	ns	$V_{GS} = -4 \text{ V}, I_{D} = -3 \text{ A}$
Rise time	t _r	_	170	_	ns	$V_{DD} \cong -10 \text{ V}$
Turn-off delay time	t _{d(off)}	_	40	_	ns	_
Fall time	t _f	_	65	_	ns	_
Body-drain diode forward voltage	V_{DF}	_	- 0.9	- 1.4	V	$IF = -5 A$, $V_{GS} = 0$ Note3
Body-drain diode reverse recovery time	t _{rr}		55		ns	$IF = -5 A, V_{GS} = 0$ diF/ dt = 20 A/ μ s

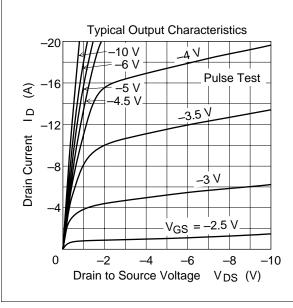
Note: 3. Pulse test

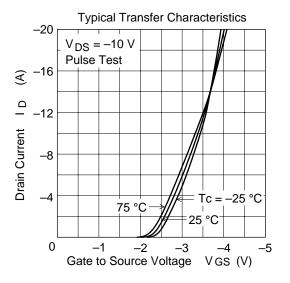
Main Characteristics

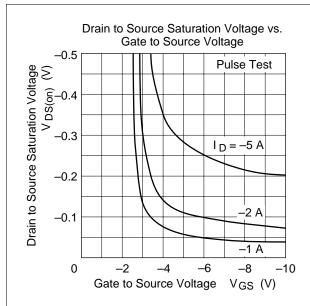


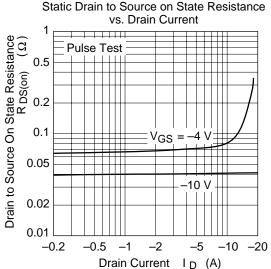


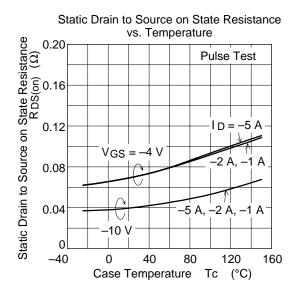
Note 4:
When using the glass epoxy board (FR4 40 x 40 x 1.6 mm)

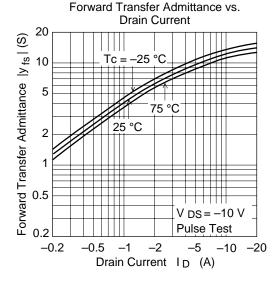


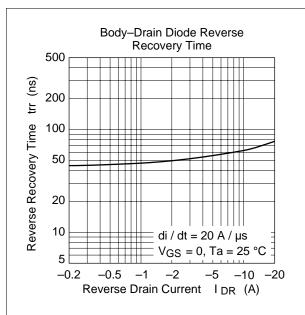


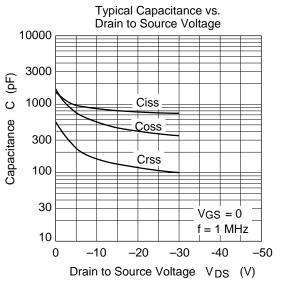


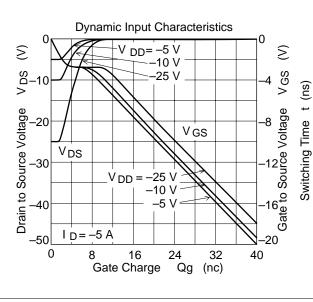


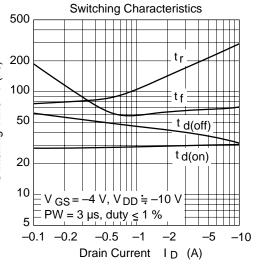


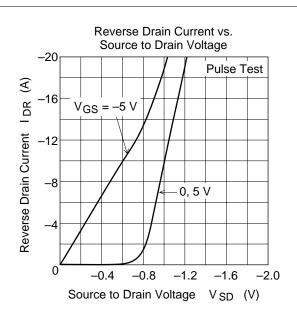


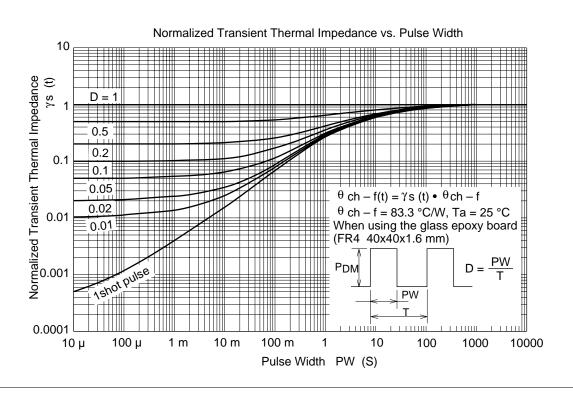


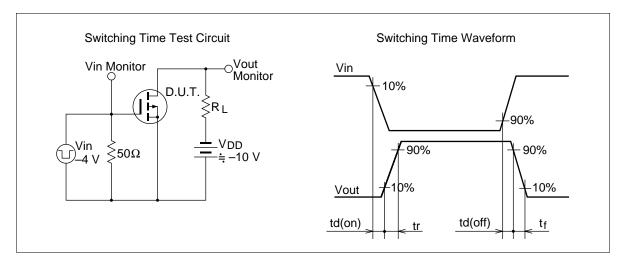






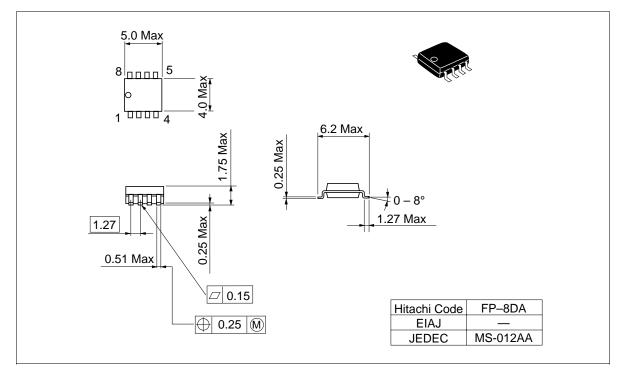






Package Dimensions

Unit: mm



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom

Tel: <44> (1628) 585000 Fax: <44> (1628) 778322 Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180 Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: -8525/2) 735 9218

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HTACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead

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